

In the Specification

On page 58, please replace Table 8 with the following amended Table:

Table 8

Display devices 10

	Charge generation layer 15-0				Q/Y(cd/A)
	First layer	Film thickness (Å)	Second layer	Film thickness (Å)	
Ex. 1	Li ₂ SiO ₃	15	-	-	7.98
Ex. 2	Li ₂ SiO ₃ + EGCHHL004 STRUCTURAL FORMULA (I)- 10 (4-1)	15	-	-	7.98
Ex. 3	Li ₂ SiO ₃ + EGCHHL004 STRUCTURAL FORMULA (I)- 10 (4-1)	30	-	-	7.75
Ex. 4	Li ₂ SiO ₃	15	Li ₂ SiO ₃ + EGCHHL004 STRUCTURAL FORMULA (I)- 10 (4-1)	15	8.11
Comp. Ex. 1	Li ₂ SiO ₃	15	V ₂ O ₅	20	8.24
Comp. Ex. 2	Li ₂ SiO ₃	15	V ₂ O ₅	15	8.13
Comp. Ex. 3	Li ₂ SiO ₃	15	V ₂ O ₅	10	7.95
Comp. Ex. 4	Li ₂ SiO ₃	15	V ₂ O ₅	5	7.59
Comp. Ex. 5	-	-	-	-	5.67
Comp. Ex. 6	Mono unit type				5.23

On page 59, please replace paragraph 1 with the following amended paragraph:

In Example 1, Li_2SiO_3 was deposited at a film thickness of 15 Å to form a charge generation layer 15-0 of a single layer structure. In Examples 2 and 3, Li_2SiO_3 and ~~LGCHL001~~ STRUCTURAL FORMULA (1)-10, a hole injection material, were coevaporated to form at the respective film thicknesses charge generation layers 15-0 of a single-layer structure which were composed of mixed layers, respectively. The composition was set at Li_2SiO_3 :~~LGCHL001~~ STRUCTURAL FORMULA (1)-10 = 4:1 (film thickness ratio). In Example 4, a charge generation layer 15-0 was formed with a second layer formed of a mixed layer of Li_2SiO_3 :~~LGCHL001~~ STRUCTURAL FORMULA (1)-10 = 4:1 (film thickness ratio) and stacked over a first layer composed of Li_2SiO_3 .